

ABSTRACT

The capacity measuring device comprises a transistor (40) formed on a silicon substrate and having a drain, source, and gate regions (41, 42, and 43), extension metals (51-54) to be connected to the regions, a guard electrode (55) surrounding the extension metal (53) for the gate region, measurement pads (61-64) electrically connected to the extension metals, the guard rings (61g-64g) surrounding the measurement pads and connected to the guard electrode (55). Accordingly, the infinitesimal capacity between any regions of the transistor in full scale is accurately measured by connecting the guard electrode (55) to a guard terminal of an infinitesimal capacity measuring apparatus for canceling the parasitic capacity.